

ABSTRACT

WAFER PRODUCING METHOD AND WAFER PRODUCING APPARATUS

A wafer producing method for producing a wafer from a hexagonal single crystal ingot. The wafer producing method includes: a planarization step of planarizing an upper surface of the hexagonal single crystal ingot; a production history forming step of applying a laser beam of such a wavelength as to be transmitted through the hexagonal single crystal ingot to the hexagonal single crystal ingot, with a focal point of the laser beam positioned in an inside of a region not to be formed with devices of a wafer to be produced from the upper surface of the hexagonal single crystal ingot which has been planarized, to form a production history; and an exfoliation layer forming step of applying a laser beam of such a wavelength as to be transmitted through the hexagonal single crystal ingot to the hexagonal single crystal ingot, with a focal point of the laser beam positioned at a depth corresponding to a thickness of the wafer to be produced from the upper surface of the hexagonal single crystal ingot which has been planarized, to form an exfoliation layer.

(Figure 19A)